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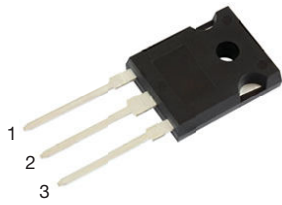
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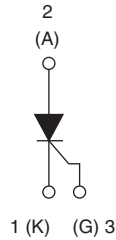
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Thyristor High Voltage, Phase Control SCR, 30 A



TO-247AD 3L



FEATURES

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-30TPS12LHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	20 A
V_{DRM}/V_{RRM}	1200 V
V_{TM}	1.3 V
I_{GT}	45 mA
T_J	-40 °C to 125 °C
Package	TO-247AD 3L
Circuit configuration	Single SCR

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	20	A
I_{RMS}		30	
V_{RRM}/V_{DRM}		1200	V
I_{TSM}		300	A
V_T	20 A, $T_J = 25\text{ °C}$	1.3	V
dv/dt		500	V/ μ s
di/dt		150	A/ μ s
T_J		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} / V_{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} / I_{DRM} AT 125 °C mA
VS-30TPS12LHM3	1200	1300	10



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 95\text{ }^\circ\text{C}$, 180° conduction half sine wave	20	A	
Maximum RMS on-state current	I_{RMS}		30		
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	250		
		10 ms sine pulse, no voltage reapplied	300		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	310	A^2s	
		10 ms sine pulse, no voltage reapplied	442		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied	4420	$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	20 A, $T_J = 25\text{ }^\circ\text{C}$	1.3	V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	12	$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.0	V	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = \text{rated } V_{RRM} / V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.5	mA
			$T_J = 125\text{ }^\circ\text{C}$	10	
Maximum holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	150		
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ maximum}$, linear to 80 % V_{DRM} , $R_g\text{-k} = \text{open}$	500	$V/\mu s$	
Maximum rate of rise of turned-on current	dI/dt		150	$A/\mu s$	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	60	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	45	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	20	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{rated value}$	0.25	
Maximum DC gate current not to trigger	I_{GD}		2.0	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	t_q		110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.8	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		40	
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.2	
Approximate weight			6	g
			0.21	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-247AD 3L	30TPS12LH	

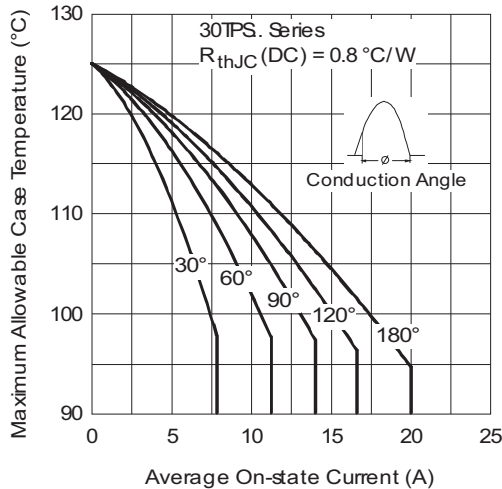


Fig. 1 - Current Rating Characteristics

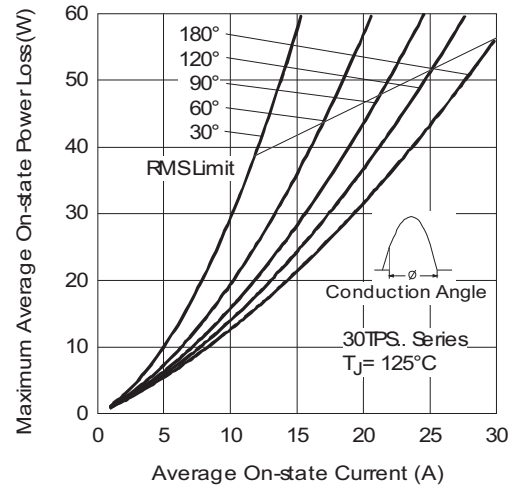


Fig. 3 - On-State Power Loss Characteristics

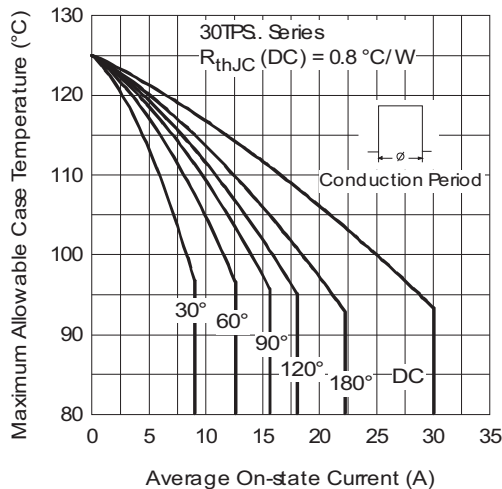


Fig. 2 - Current Rating Characteristics

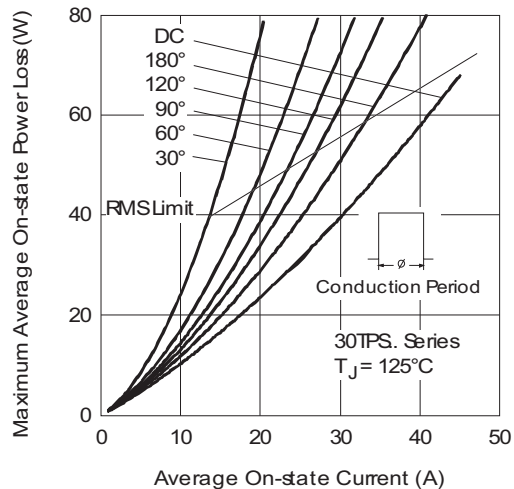


Fig. 4 - On-State Power Loss Characteristics

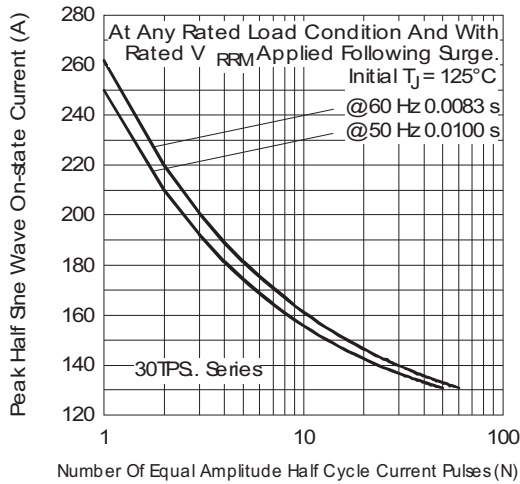


Fig. 5 - Maximum Non-Repetitive Surge Current

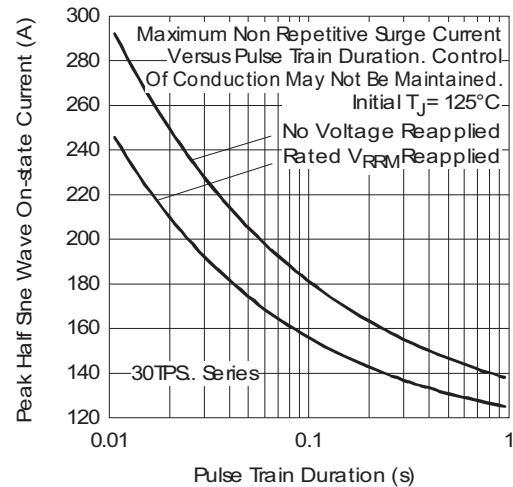


Fig. 6 - Maximum Non-Repetitive Surge Current

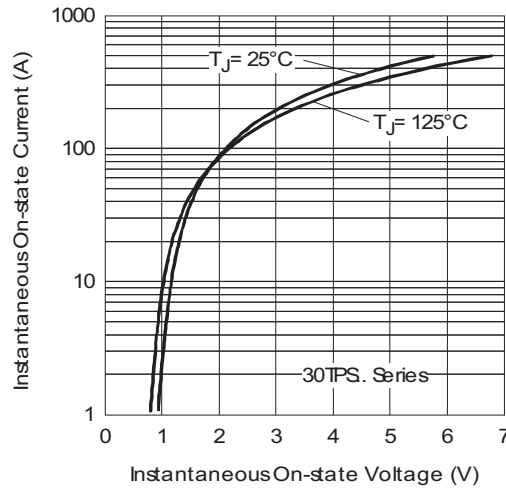


Fig. 7 - On-State Voltage Drop Characteristics

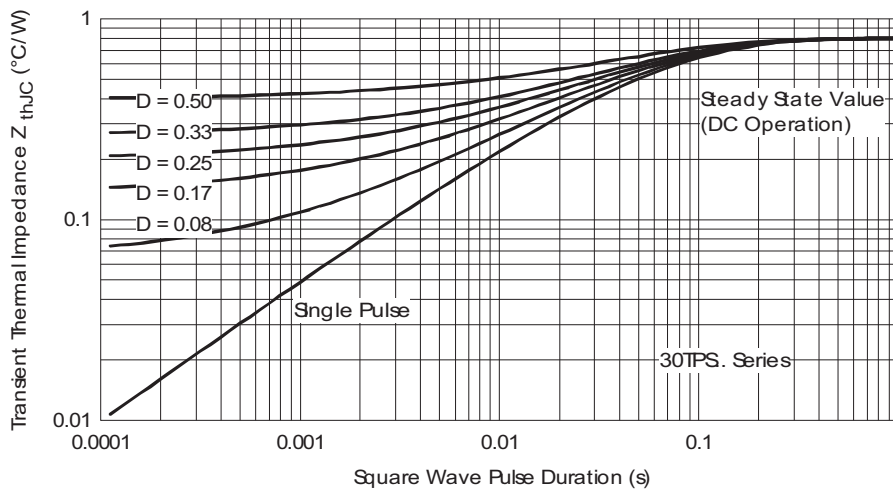


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

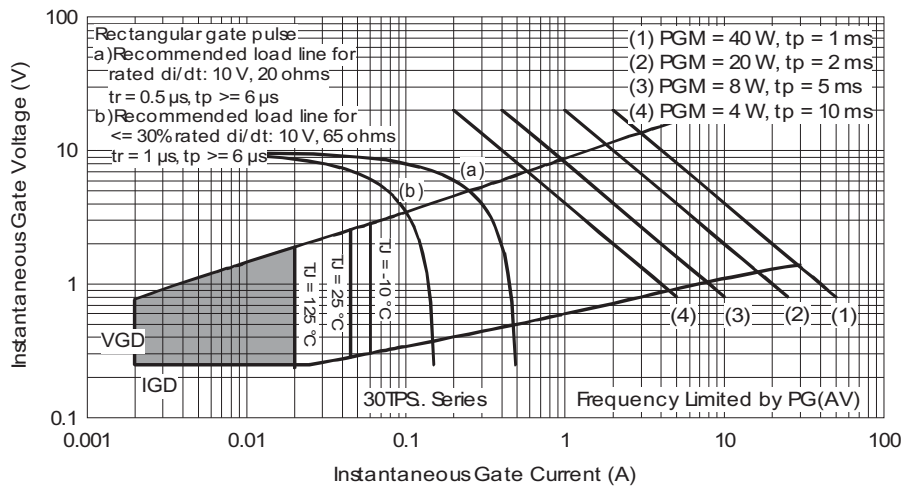


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	30	T	P	S	12	L	H	M3
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating (30 = 30 A)
- 3** - Circuit configuration:
T = Thyristor
- 4** - P = TO-247 package
- 5** - Type of silicon:
S = Standard recovery rectifier
- 6** - Voltage code x 100 = V_{RRM} ——— **12 = 1200 V**
- 7** - Package L = long lead
- 8** - H = AEC-Q101 qualified
- 9** - Environmental digit:
M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-30TPS12LHM3	25	500	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS		
Dimensions	TO-247AD 3L	www.vishay.com/doc?95626
Part marking information	TO-247AD 3L	www.vishay.com/doc?95007



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